

FORM PTO-1449

U.S. DEPARTMENT OF COMMERCE
PATENT AND TRADEMARK OFFICEATTY. DOCKET NO.
ASMMC.020AUSAPPLICATION NO.
09/997,396INFORMATION DISCLOSURE STATEMENT
BY APPLICANT

(USE SEVERAL SHEETS IF NECESSARY)

APPLICANT
Hujanen et al.FILING DATE
November 28, 2001GROUP
2818EXAMINER
INITIAL

OTHER DOCUMENTS (INCLUDING AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.)

DV

1. Yagishita et al., "Cleaning of Copper Surface Using Vapor-Phase Organic Acids," Materials Researching Society Spring 2003 Meeting, Symposium E, Session E, Paper E3.28

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EXAMINER

Shuland

DATE CONSIDERED

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U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE (IF APPROPRIATE)
DV	1	5,382,333	01/17/95	Ando et al.			

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FOREIGN PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
							YES	NO
DV	1	JP 62221102	09/29/87	Japan Patent Abstract			x	
	2	WO 02/09158 A2	07/18/01	PCT				
	3	WO 02/09126 A2	07/18/01	PCT				
DV	4	WO 01/88972 A1	05/15/01	PCT				

EXAMINER INITIAL	OTHER DOCUMENTS (INCLUDING AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.)							
DV	5	XP-002223616, "5 th Asian Symposium on Information Storage Technology (ASIST), Hong Kong, China, 14-16" Nov. 2000						
	6	Utriainen et al., "Studies of metallic thin film growth in an atomic layer epitaxy reactor using M(acac) ₂ (M_Ni, Cu, Pt) precursors", Applied Surface Science, April 2000						
	7	Ritala et al., "Atomic layer epitaxy - a valuable tool for nanotechnology?" Nanotechnology 10 (1999), P 19-24						
DV	8	Oral presentation Chang-Wook Jeong (SEOUL NATIONAL UNIVERSITY CENTER FOR ADVANCED MATERIALS RES.) : "Thursday, 16/11/2000: Magnetoresistance of ferromagnetic tunneljunctions with A1202 formed by Plasma-Assisted Atomic Layer Controlled Deposition" Presentation at 5 th Asian Symposium on Information Storage Technology (ASIST). November 16, 2000						

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